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# SEVENTH SEMESTER B.TECH. (ENGINEERING) [09 EXAMINATION, NOVEMBER 2016

## EC/PTEC 09 702-MICROWAVE ENGINEERING

Time : Three Hours

### Maximum: 70 Marks

Name.... Reg. No.

SCHEME

Part A

- I. Answer all questions :
  - 1 Discuss about the diagonal elements for perfect matched network.
  - 2 A 20 mW signal is fed into one of the collinear port 1 of a lossless H plane Tee Junction.Calculate power delivered through port 1 when other ports are terminated in matched line.
  - 3 Compare TWTA and Klystron Amplifier.
  - 4 List high frequency limitation of bipolar devices.
  - 5 List the properties of dielectric materials.

 $(5 \times 2 = 10 \text{ marks})$ 

#### Part B

#### II. Answer any *four* questions :

- 6 Find the S Matrix of a length L of a lossless transmission line terminated by matched impedance.
- 7 Explain Velocity Modulation.
- 8 The Drift velocity of electrons is  $2 \times 10^{-1}$  cm/s through the active region of length  $10 \times 10^{-4}$ cm. Calculate the natural frequency and critical voltage of the Gunn diode.
- 9 Calculate the planar resistance for the resistive film length of 10 mm, width of 5 mm, thickness of. 1 micrometer and sheet resistivity of film is  $2.4 \times 10^{-8}$  mho-m.
- 10 Discuss the working principle of backward diode.
- 11 With neat schematic block diagram explain Network Analyzer.

 $(4 \times 5 = 20 \text{ marks})$ 

#### Part C '

#### III. Answer all questions :

12. (a) Explain in detail about Magic Tee and also list its application.

Or

(b) State the properties of Circulator and also explain its working principle.

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13 (a) (i) With neat functional diagram explain the mechanism of oscillations in klystron. (7 marks)

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(ii) Derive the expression for output power in Reflex Klystron.

(3 marks)

### Or

- (b) Explain in detail about the construction and operation of Magnetron.
- 14 (a) Discuss about PIN Diode and its characteristics.

## Or

(b) (i) Explain the modes of operation in Gunn Diode.

(ii) List the advantage of upconverter over negative resistance device.

(3 marks)

(7 marks)

15 (a) Explain in detail about hybrid technology.

## Or

(b) Explain the experimental setup and possible source of error in VSWR measurement.

 $[4 \times 10 = 40 \text{ marks}]$